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ILNAS-EN IEC 62228-5:2021

Integrated circuits - EMC evaluation of transceivers - Part 5: Ethernet transceivers

Circuits intégrés - Évaluation de la CEM
des émetteurs-récepteurs - Partie 5 :
Émetteurs-récepteurs

Integrierte Schaltungen - Bewertung der
elektromagnetischen Verträglichkeit von
Sende-Empfangsgeräten - Teil 5:
Ethernet-Sende-Empfangsgerät

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National Foreword

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ILNAS-EN IEC 62228-5:2021

EUROPEAN STANDARD **EN IEC 62228-5**
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**Integrated circuits - EMC evaluation of transceivers - Part 5:
Ethernet transceivers
(IEC 62228-5:2021)**

Circuits intégrés - Évaluation de la CEM des émetteurs-
récepteurs - Partie 5 : Émetteurs-récepteurs
(IEC 62228-5:2021)

Integrierte Schaltungen - Bewertung der
elektromagnetischen Verträglichkeit von Sende-
Empfangsgeräten - Teil 5: Ethernet-Sende-Empfangsgerät
(IEC 62228-5:2021)

This European Standard was approved by CENELEC on 2021-05-31. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this European Standard the status of a national standard without any alteration.

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European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

CEN-CENELEC Management Centre: Rue de la Science 23, B-1040 Brussels

European foreword

The text of document 47A/1115/FDIS, future edition 1 of IEC 62228-5, prepared by SC 47A "Integrated circuits" of IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 62228-5:2021.

The following dates are fixed:

- latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2022-02-28
- latest date by which the national standards conflicting with the document have to be withdrawn (dow) 2024-05-31

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Endorsement notice

The text of the International Standard IEC 62228-5:2021 was approved by CENELEC as a European Standard without any modification.

In the official version, for Bibliography, the following notes have to be added for the standards indicated:

CISPR 16-1-1	NOTE	Harmonized as EN IEC 55016-1-1
IEC 61000-4-2	NOTE	Harmonized as EN 61000-4-2
IEC 61000-4-4	NOTE	Harmonized as EN 61000-4-4
IEC 61000-4-5	NOTE	Harmonized as EN 61000-4-5
IEC 61967-2	NOTE	Harmonized as EN 61967-2
IEC 61967-8	NOTE	Harmonized as EN 61967-8
IEC 62132-2	NOTE	Harmonized as EN 62132-2
IEC 62132-8	NOTE	Harmonized as EN 62132-8

Annex ZA (normative)

Normative references to international publications with their corresponding European publications

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE 1 Where an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here: www.cenelec.eu.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 61967-1	-	Integrated circuits - Measurement of electromagnetic emissions - Part 1: General conditions and definitions	EN IEC 61967-1	-
IEC 61967-4	-	Integrated circuits - Measurement of electromagnetic emissions - Part 4: Measurement of conducted emissions - 1 ohm/150 ohm direct coupling method	EN IEC 61967-4	-
IEC 62132-1	-	Integrated circuits - Measurement of electromagnetic immunity - Part 1: General conditions and definitions	EN 62132-1	-
IEC 62132-4	-	Integrated circuits - Measurement of electromagnetic immunity 150 kHz to 1 GHz - Part 4: Direct RF power injection method	EN 62132-4	-
IEC 62215-3	-	Integrated circuits - Measurement of impulse immunity - Part 3: Non-synchronous transient injection method	EN 62215-3	-
IEC 62228-1	-	Integrated circuits – EMC evaluation of transceivers – Part 1: General conditions and definitions	EN IEC 62228-1	-
ISO 10605	-	Road vehicles - Test methods for electrical disturbances from electrostatic discharge	-	-
ISO 21111-2	-	Road vehicles - In-vehicle Ethernet - Part 2: Common physical entity requirements	-	-
ISO 7637-2	-	Road vehicles - Electrical disturbances from conduction and coupling – Part 2: Electrical transient conduction along supply lines only	-	-

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
ISO/IEC/IEEE 8802-3	2017	Information technology Telecommunications and information exchange between systems - Local and metropolitan area networks - Specific requirements - Part 3: Standard for Ethernet	-	-
+A1	2017		-	-
+A4	2017		-	-
EIA-198-1	-	Electronic Components Industry Association - Ceramic Dielectric Capacitors Classes I, II, III and IV	-	-



INTERNATIONAL STANDARD



Integrated circuits – EMC evaluation of transceivers – Part 5: Ethernet transceivers

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